

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D Max (Note 6)
20V	175mΩ @ V _{GS} = 4.5V	1.40A @ T _A = +25°C
	240mΩ @ V _{GS} = 2.5V	1.20A @ T _A = +25°C
	360mΩ @ V _{GS} = 1.8V	1.0A @ T _A = +25°C

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

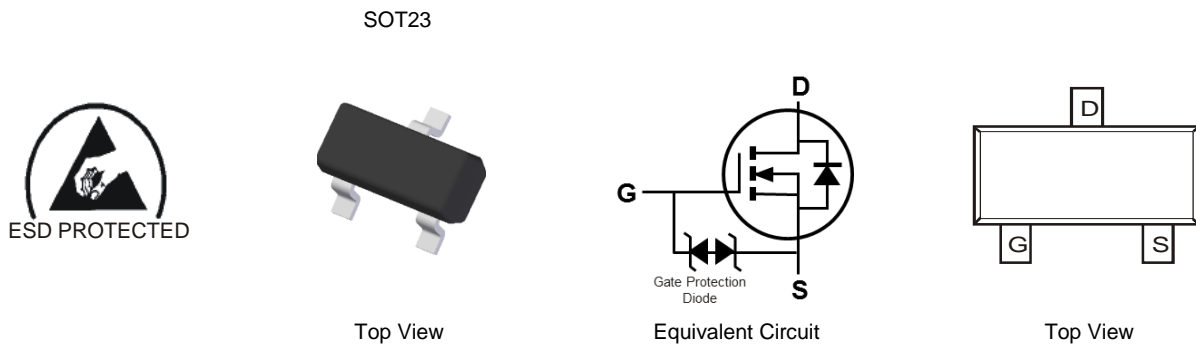
- Load Switch

Features and Benefits

- On Resistance <200mΩ
- Low Gate Threshold Voltage
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **ESD Protected Gate**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.08 grams (Approximate)

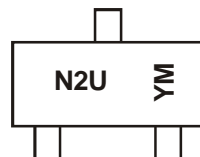


Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMN2300U-7	N2U	7	8	3000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



N2U = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: G = 2019)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	~	2019	2020	2021	2022	2023
Code	Y	~	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current	Steady State	T _A = +25°C (Note 6)	I _D	1.40	A
		T _A = +85°C (Note 6)		1.01	
		T _A = +25°C (Note 5)		1.24	
Pulsed Drain Current (Note 7)			I _{DM}	11	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	0.43	W
	(Note 6)		0.55	W
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	288	°C/W
	(Note 6)		228	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on 25mm × 25mm square copper plate with FR-4 substrate PC board, 2oz copper.
 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

Thermal Characteristics

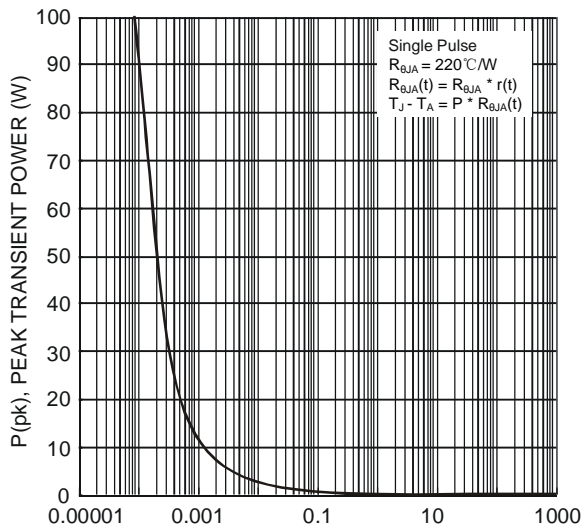


Fig. 1 Single Maximum Power Dissipation

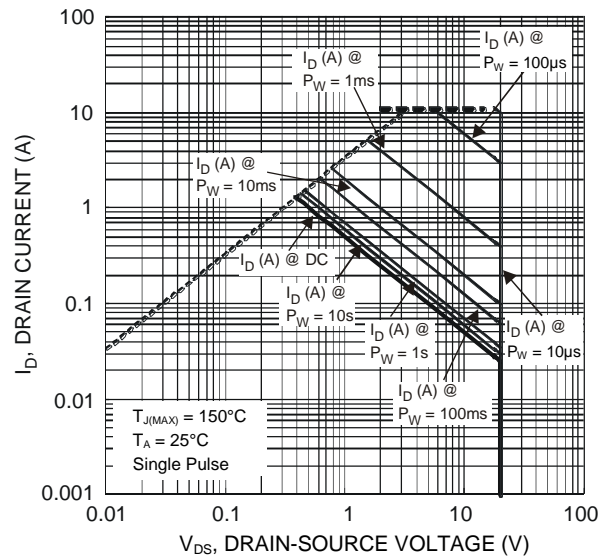


Fig. 2 SOA, Safe Operation Area

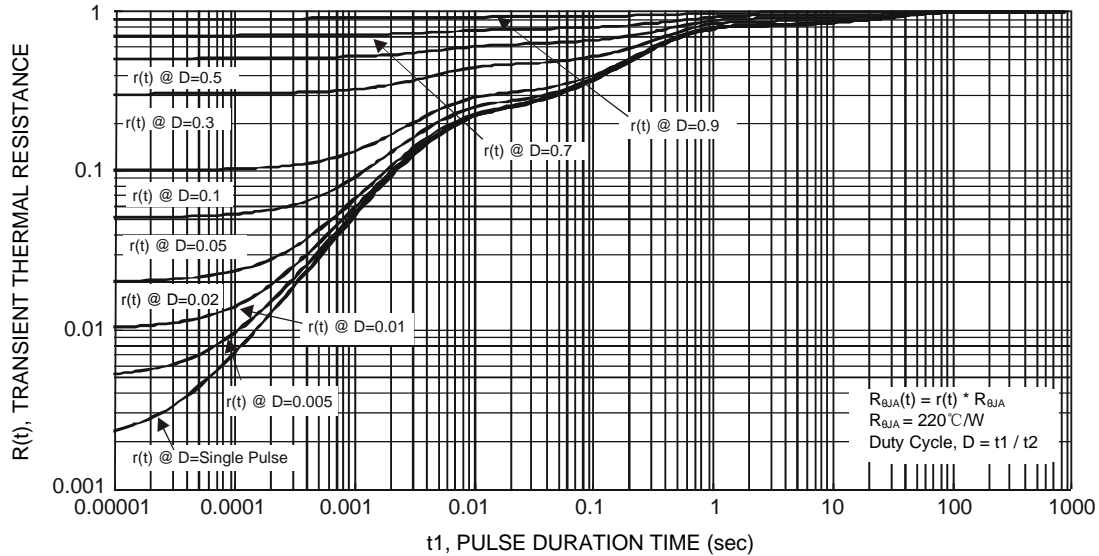


Fig. 3 Transient Thermal Resistance

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.45	—	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	175	mΩ	V _{GS} = 4.5V, I _D = 300mA
				240		V _{GS} = 2.5V, I _D = 250mA
				360		V _{GS} = 1.8V, I _D = 100mA
Forward Transfer Admittance	Y _{fs}	40	—	—	mS	V _{DS} = 3V, I _D = 30mA
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	67.6	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	9.7	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	7.5	—	pF	
Gate Resistance	R _g	—	70	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	1.6	—	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 1A
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.5	—	ns	V _{DS} = 10V, I _D = 1A V _{GS} = 10V, R _G = 6Ω
Turn-On Rise Time	t _R	—	2.8	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	38	—	ns	
Turn-Off Fall Time	t _F	—	13	—	ns	

Note: 8. Short duration pulse test used to minimize self-heating effect.

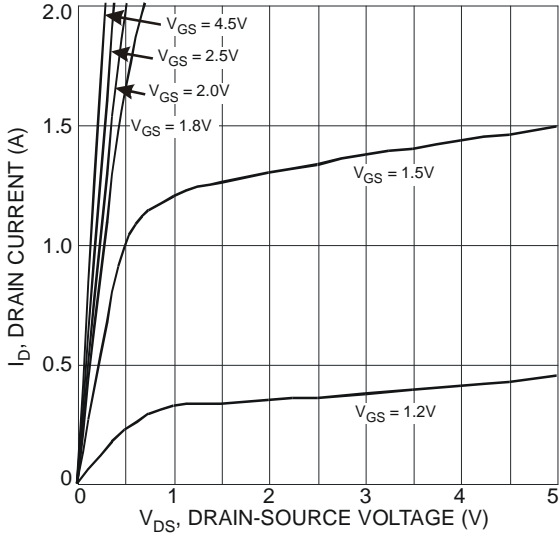


Fig. 4 Typical Output Characteristic

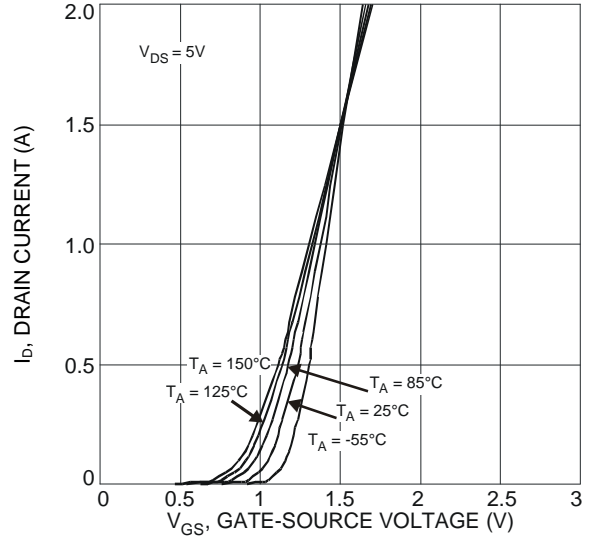


Fig. 5 Typical Transfer Characteristic

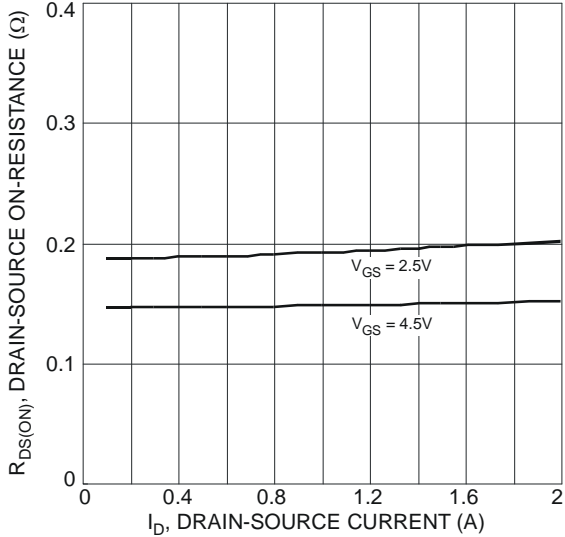


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

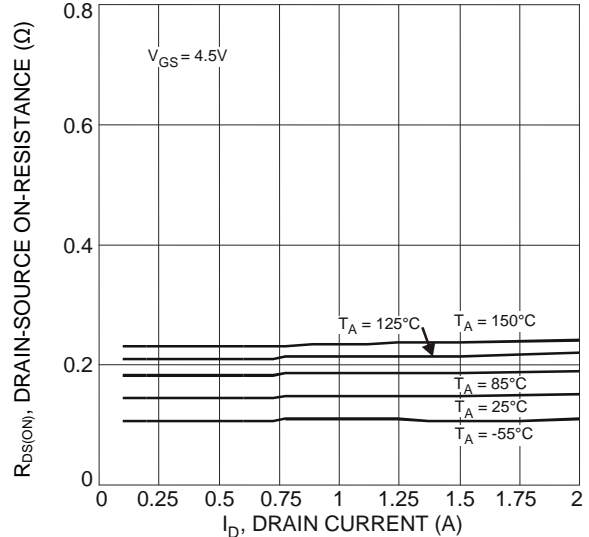


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

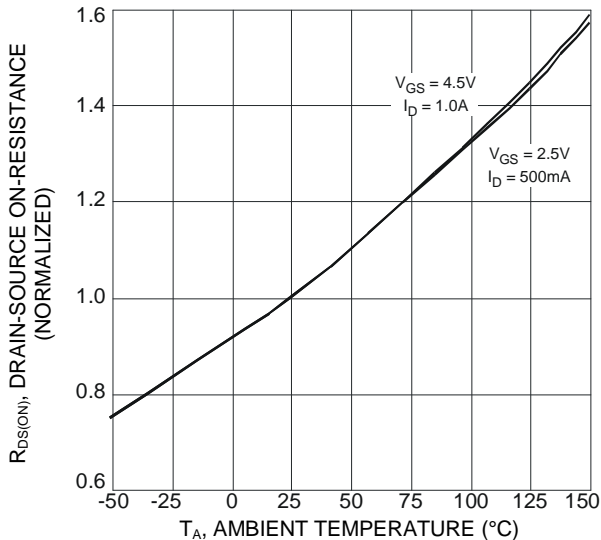


Fig. 8 On-Resistance Variation with Temperature

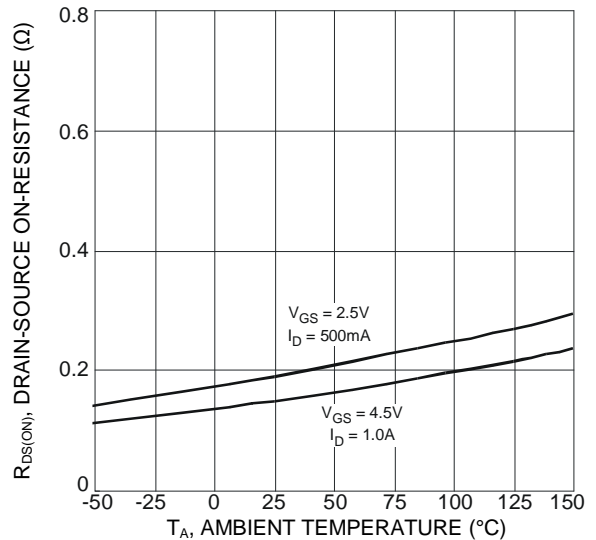


Fig. 9 On-Resistance Variation with Temperature

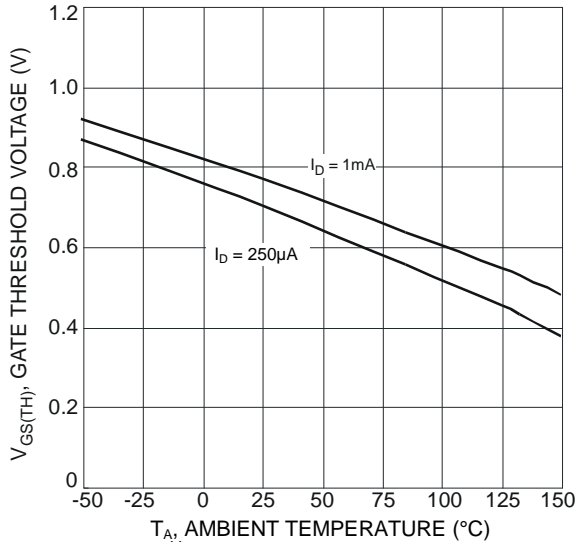


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

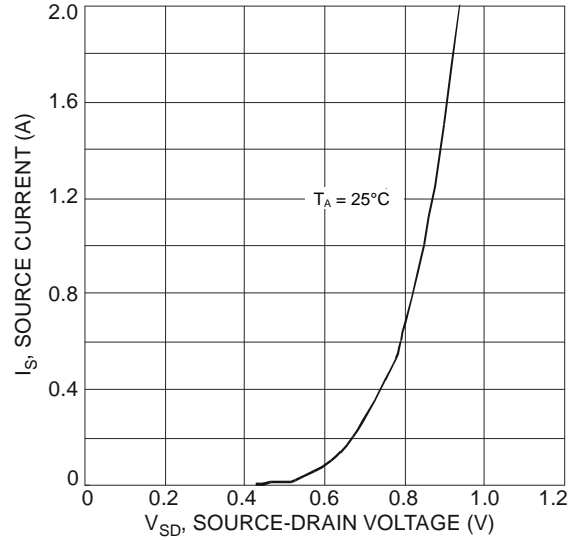


Fig. 11 Diode Forward Voltage vs. Current

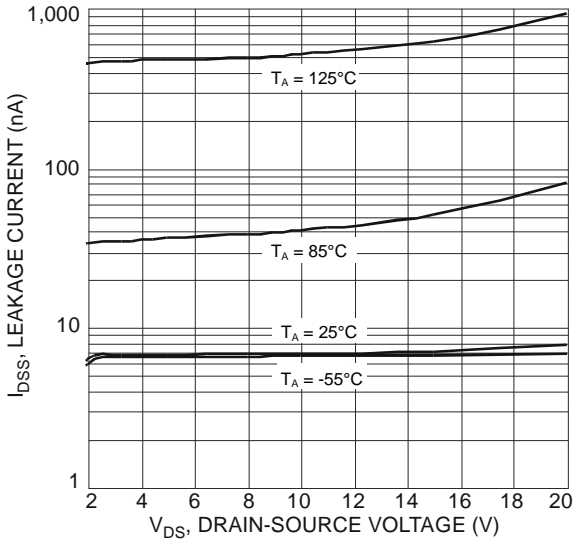


Fig. 12 Typical Leakage Current vs. Drain-Source Voltage

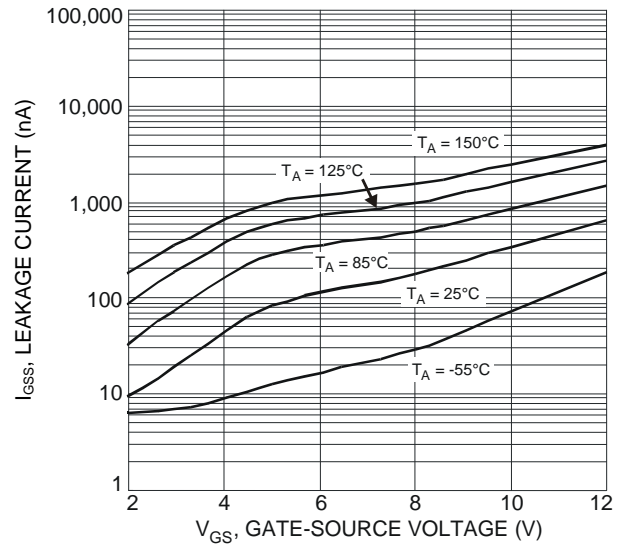


Fig. 13 Leakage Current vs. Gate-Source Voltage

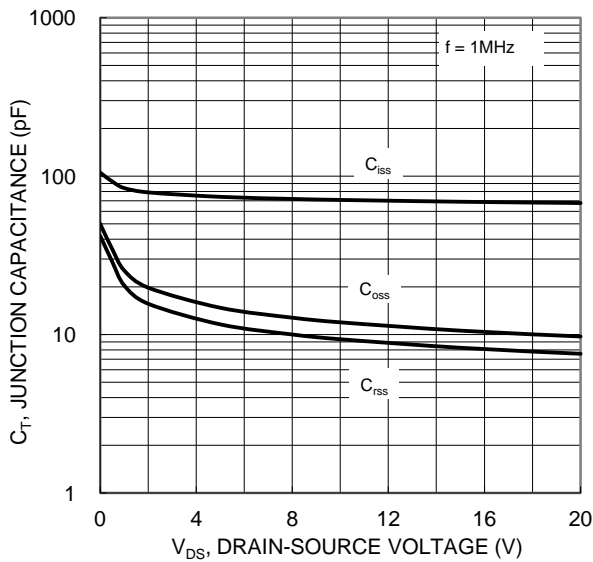


Fig. 14 Typical Junction Capacitance

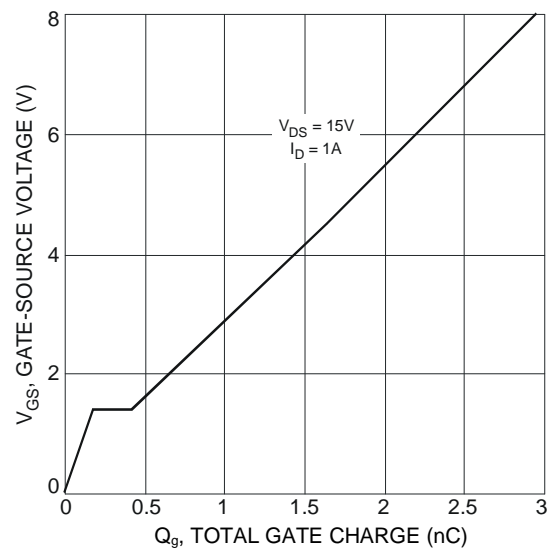
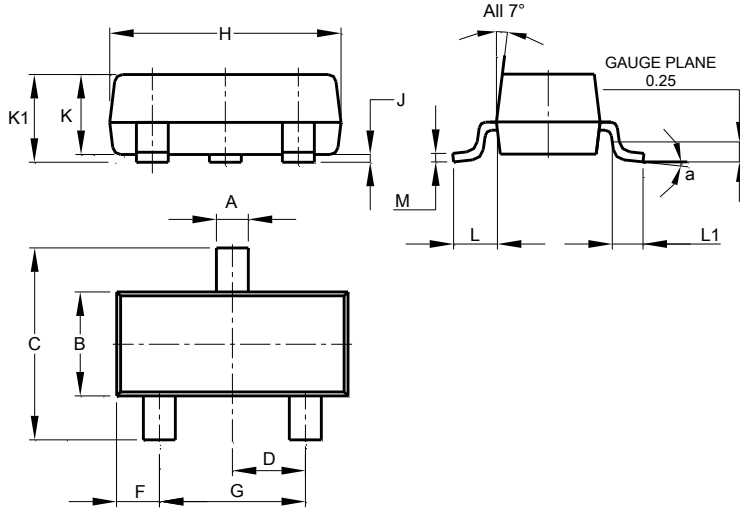


Fig. 15 Gate Charge Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

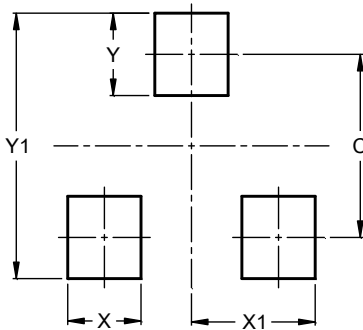


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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